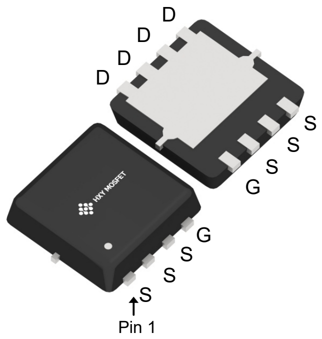
HUAXUANYANG HXY
ELECTRONICS CO.,LTD

BSZ0910LSATMA1

N-Channel Enhancement Mode MOSFET

Description

The BSZ0910LSATMA1 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

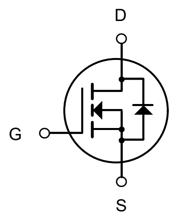


DFN3X3-8L

General Features

V_{DS} = 30V I_D = 90A

$R_{DS(ON)}$ < 4.6 mΩ @ V_{GS}=10V



N-Channel MOSFET

Application

Battery protection

Load switch

Uninterruptible power supply

Ordering Information

Product ID	**Pack**	**Brand**	**Qty(PCS)**
BSZ0910LSATMA1	DFN3X3-8L	HXY MOSFET	5000

Absolute Maximum Ratings (T_C=25°C unless otherwise noted)

Symbol	Parameter	Rating	Units
VDS	Drain-Source Voltage	30	V
VGS	Gate-Source Voltage	±20	V
I_D@T_C=25˚C	Continuous Drain Current, V_{GS} @ 10V[1]	90	A
I_D@T_C=75˚C	Continuous Drain Current, V_{GS} @ 10V[1]	45	A
IDM	Pulsed Drain Current[2]	290	A
EAS	Single Pulse Avalanche Energy[3]	196	mJ
IAS	Avalanche Current	36	A
P_D@T_C=25˚C	Total Power Dissipation[4]	46	W
TSTG	Storage Temperature Range	-55 to 175	˚C
T_J	Operating Junction Temperature Range	-55 to 175	˚C
$R_{\theta}JA$	Thermal Resistance Junction-ambient [1]	62	˚C/W
$R_{\theta}JC$	Thermal Resistance Junction-Case[1]	1.72	˚C/W

Electrical Characteristics (T_J=25°C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	30	---	---	V
$\triangle BV_{DSS}/\triangle T_J$	BV_{DSS} Temperature Coefficient	Reference to 25°C , I_D=1mA	---	---	---	V/°C
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=10V , I_D=30A	---	3.5	4.6	mΩ
		V_{GS}=4.5V , I_D=15A	---	7.8	10	
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =250uA	1.2	1.6	2.5	V
$\triangle V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	---	---	mV/°C
I_{DSS}	Drain-Source Leakage Current	V_{DS}=30V , V_{GS}=0V , T_J=25°C	---	---	1	uA
		V_{DS}=30V, V_{GS}=0V , T_J=100°C	---	---	100	
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±100	nA
gfs	Forward Transconductance	V_{DS}=10V , I_D=30A	---	80	---	S
R_g	Gate Resistance	V_{DS}=0V , V_{GS}=0V , f=1MHz	---	2	---	Ω
Q_g	Total Gate Charge	V_{DS}=15V , V_{GS}=4.5V , I_D=30A	---	20	---	nC
Q_{gs}	Gate-Source Charge		---	5	---	
Q_{gd}	Gate-Drain Charge		---	7.2	---	
$T_{d(on)}$	Turn-On Delay Time	VGS=10V, VDD=15V, RG=3Ω, ID=30A	---	9	---	ns
T_r	Rise Time		---	16	---	
$T_{d(off)}$	Turn-Off Delay Time		---	43	---	
T_f	Fall Time		---	12	---	
C_{iss}	Input Capacitance	V_{DS}=15V , V_{GS}=0V , f=1MHz	---	2088	---	pF
C_{oss}	Output Capacitance		---	277	---	
C_{rss}	Reverse Transfer Capacitance		---	209	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current[1,5]	V_G=V_D=0V , Force Current	---	---	90	A
V_{SD}	Diode Forward Voltage[2]	V_{GS}=0V , I_S=1A , T_J=25°C	---	---	1.2	V

Note :
1.The data tested by surface mounted on a 1 inch^2 FR-4 board with 2OZ copper.
2.The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%
3.The EAS data shows Max. rating . The test condition is TJ = 25°C,VDD=24V,VGS=10V,L=0.1mH,IAS=36A.
4.The power dissipation is limited by 150°C junction temperature
5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Characteristics

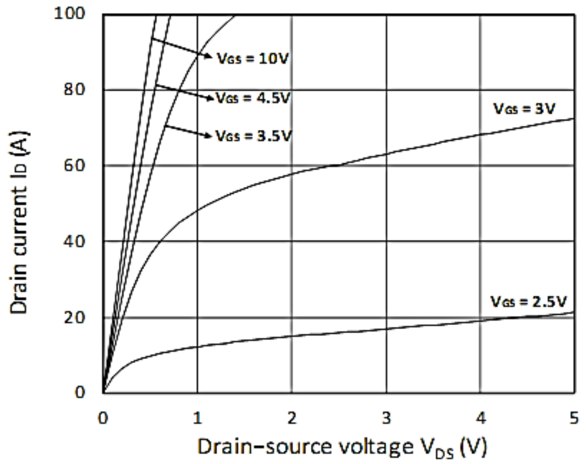


Figure 1. Output Characteristics

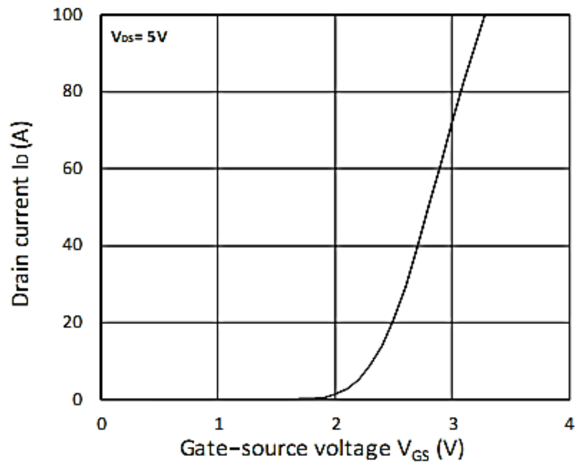


Figure 2. Transfer Characteristics

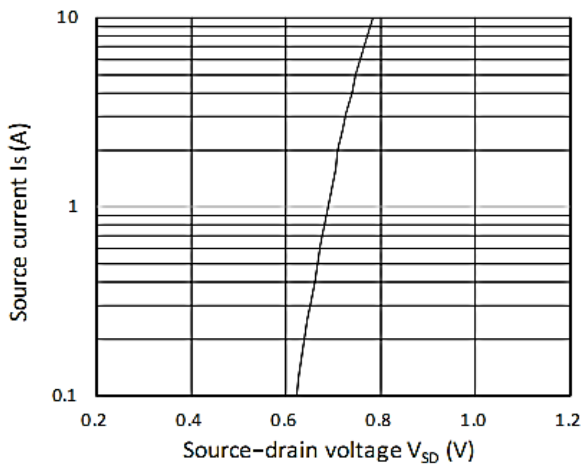


Figure 3. Forward Characteristics of Reverse

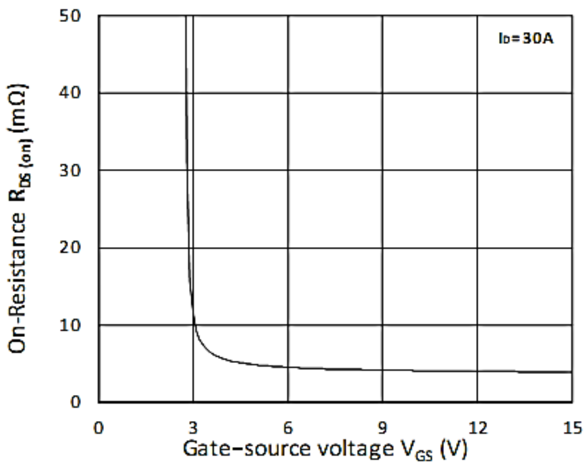


Figure 4. RDS(ON) vs. VGS

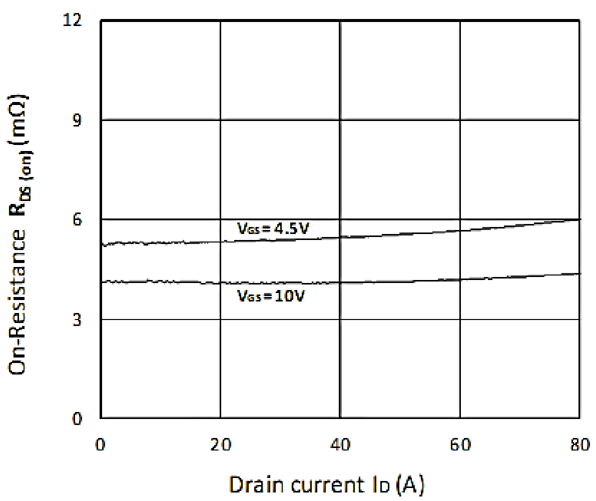


Figure 5. R DS(ON) vs. ID

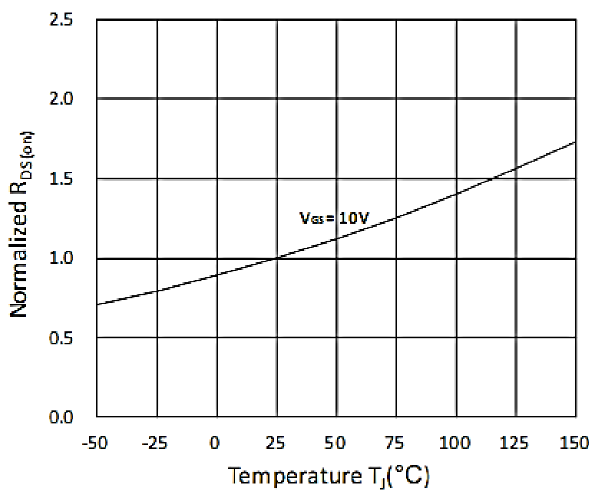


Figure 6. Normalized R DS(on) vs. Temperature

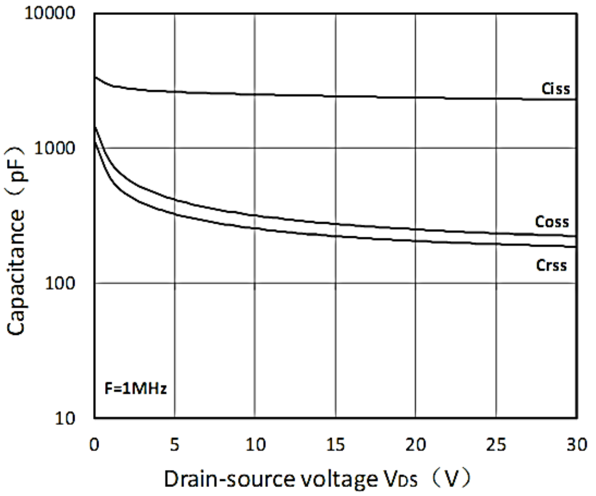


Figure 7. Capacitance Characteristics

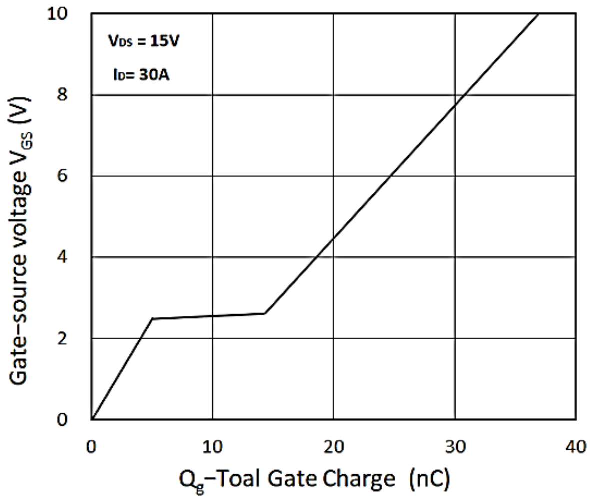
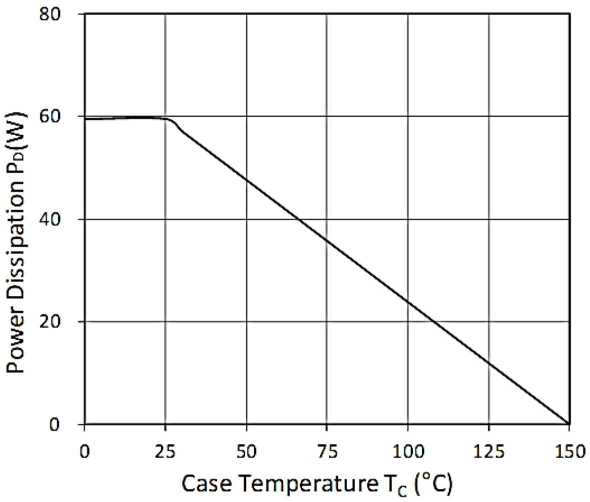


Figure 8. Gate Charge Characteristics



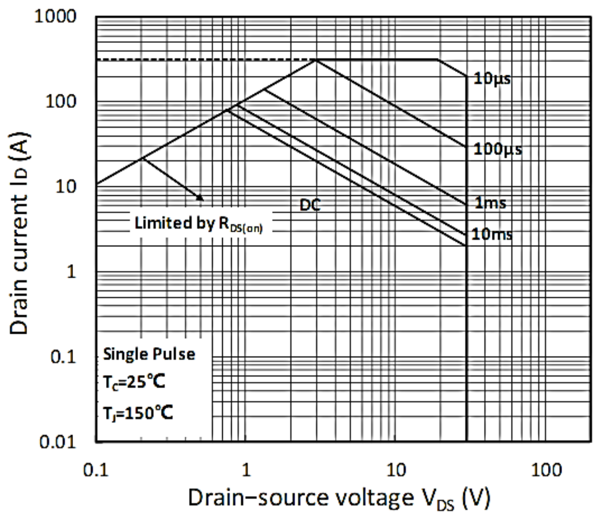


Figure 9. Power Dissipation

Figure10. Safe Operating Area

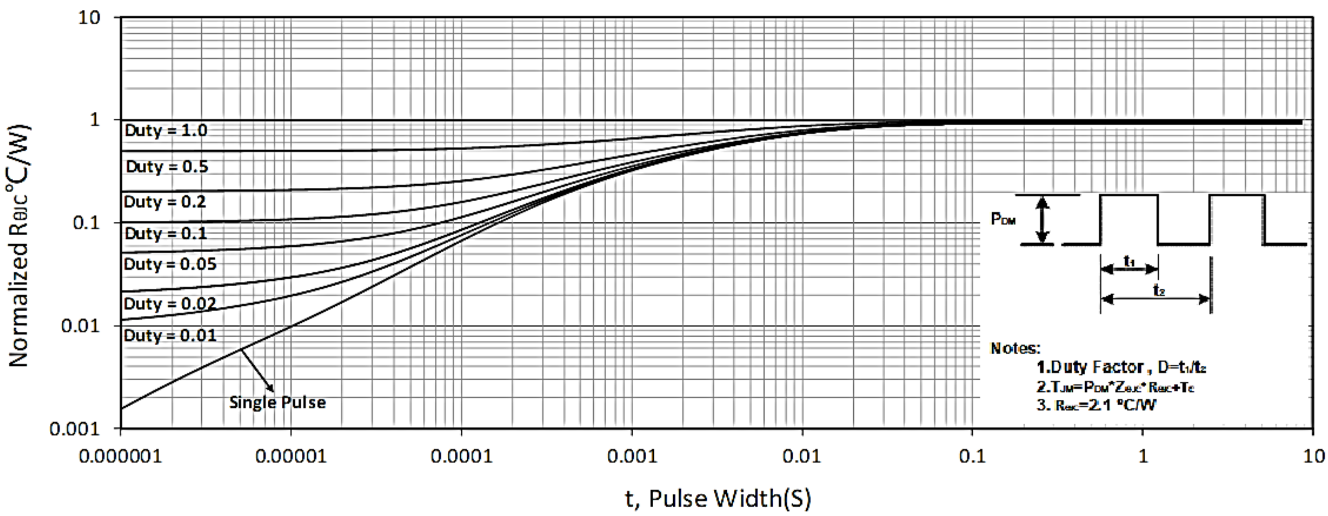
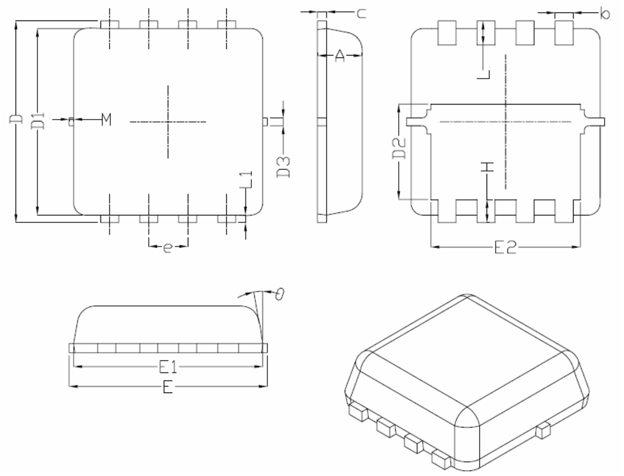


Figure 11. Normalized Maximum Transient Thermal Impedance

DFN3X3-8L Package Information



Symbol	Dimensions In Millimeters		
	Min.	Nom.	Max.
A	0.70	0.75	0.80
b	0.25	0.30	0.35
c	0.10	0.15	0.25
D	3.25	3.35	3.45
D1	3.00	3.10	3.20
D2	1.48	1.58	1.68
D3	-	0.13	-
E	3.20	3.30	3.40
E1	3.00	3.15	3.20
E2	2.39	2.49	2.59
e	0.65BSC		
H	0.30	0.39	0.50
L	0.30	0.40	0.50
L1	-	0.13	-
M	*	*	0.15
θ		10°	12°

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